

SCHOTTKY BARRIER DIODE

●Applications

Low current rectification and high speed switching

●Features

Extremely small surface mounting type.

High reliability

Low I_R .

●Construction

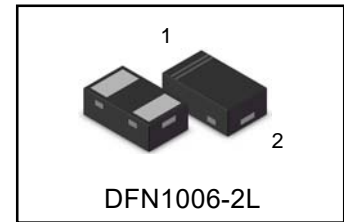
Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

Ordering Information

Device	Marking	Shipping
RB520BS-40	D1	10000/Tape&Reel

RB520BS-40



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

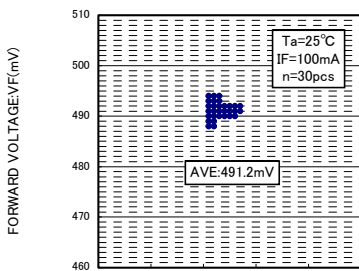
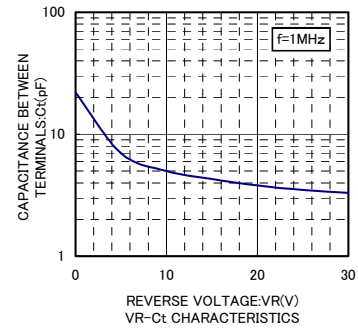
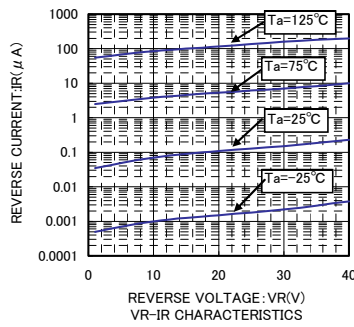
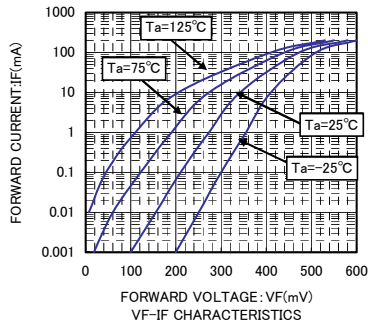
Parameter	Symbol	Limits	Unit
Reverse voltage(repetitive peak)	V_R	40	V
DC reverse voltage	V_R	40	V
Average rectified forward current	I_O	200	mA
Peak forward surge current	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS($T_A = 25^\circ\text{C}$)

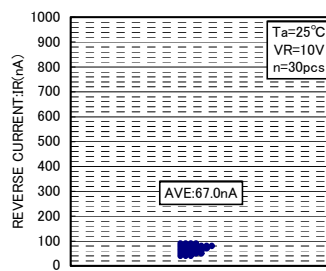
Parameter	Symbol	Min.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.39	V	$I_F = 10\text{mA}$
Forward voltage	V_F	-	0.55	V	$I_F = 100\text{mA}$
Reverse current	I_R	-	1	μA	$V_R = 10\text{V}$
Reverse current	I_R	-	10	μA	$V_R = 40\text{V}$



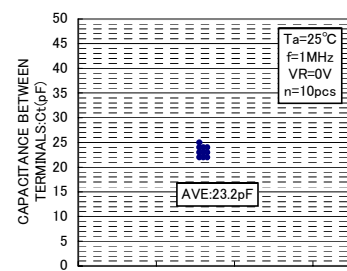
●Electrical characteristic curves



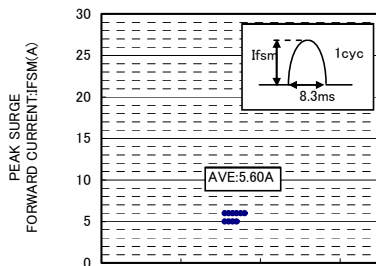
VF DISPERSION MAP



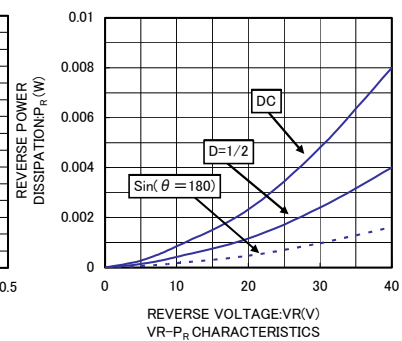
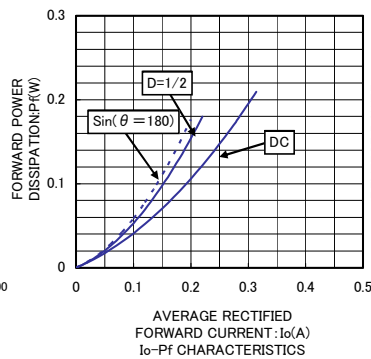
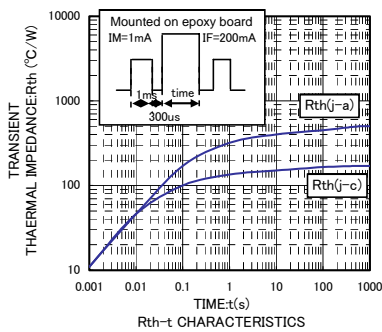
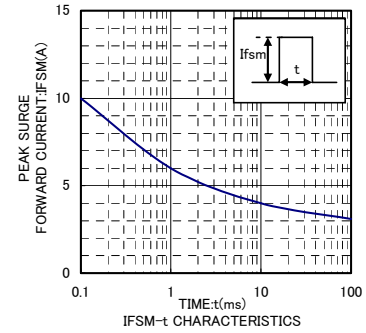
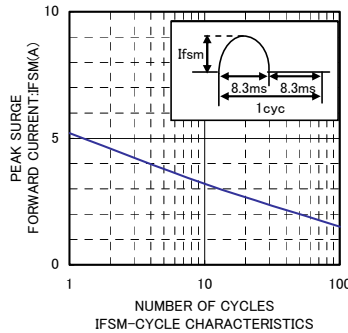
IR DISPERSION MAP

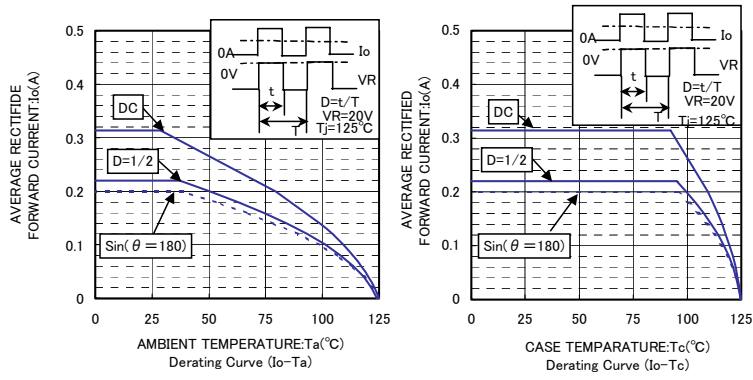


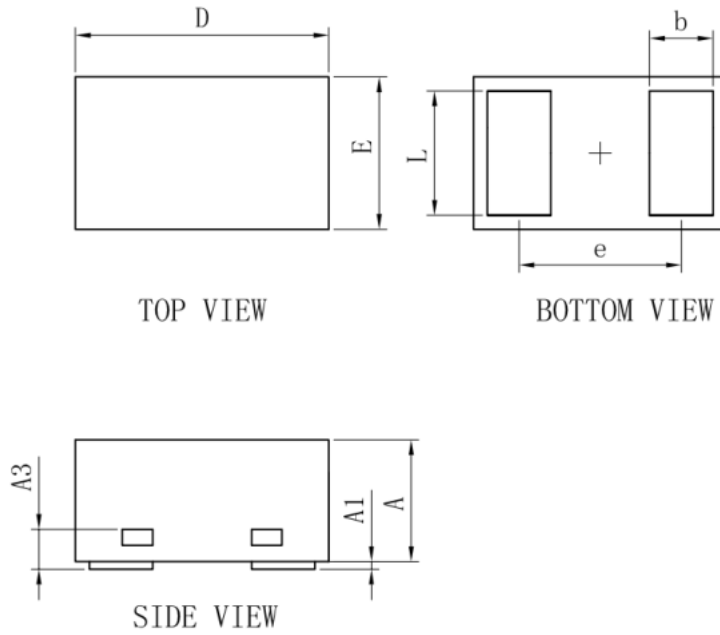
Ct DISPERSION MAP



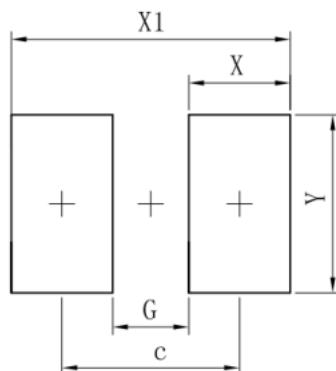
IFSM DISPERSION MAP





OUTLINE AND DIMENSIONS


Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			

SOLDERING FOOTPRINT


Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

